

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	2	("4946800").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/03 16:57
L3	40	("3100276"   "3159780"   "3209428"   "3226268"   "3235779"   "3255055"   "3317746"   "3386865"   "3397349"   "3442011"   "3457632"   "3500139"   "3534234"   "3550292"   "3586542"   "3622382"   "3648125"   "3649386"   "3663308"   "3666548"   "3707765"   "3726719").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/03 16:58
L4	209	(atomic\$4 near smooth near surface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:25
L5	54089	((metallurgical\$2 metal\$3) near bond\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:27
L6	0	4 same 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:27
L7	5	4 and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:27
L8	690362	((solid adj state) semiconductor metal gate) near (layer film material)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:31
L9	706749	((solid adj state) semiconductor metal gate field) near (layer film material)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:31

L10	17804	9 and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:35
L11	52	10 and ("40" near angstrom\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:32
L12	3	("3648125"   "4690714"   "4946800").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/03 17:35
L13	126	9 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:35
L14	12	("20020164846"   "3430109"   "3585714"   "4371406"   "4916513"   "4946800"   "5082793"   "5696402"   "6057584"   "6599781").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/03 17:39
L15	14	("3354360"   "3386865"   "3430109"   "3534234"   "3586542"   "3598664"   "3648125"   "Re28653").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/03 17:47
L16	20	("2795742"   "2813048"   "3100276"   "3124452"   "3226225"   "3267405"   "3430109"   "3434827"   "3500135"   "3765956"   "4136435").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/03 17:48
S1	2	("5874175").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/03 16:57
S2	15	("2667432"   "3215555"   "3901772"   "3915369"   "4252856"   "4396677"   "4608226"   "4624403"   "4776862"   "4890783"   "5161728"   "5273731"   "5551277").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/21 11:02
S3	6	("3132044"   "3805372"   "4348131"   "4710235"   "4757934").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/21 11:05
S4	0	("(((solidadjstate)semiconductormetalgate)near(layerfilmmaterial))with(nonearmorenear40.0nearangstrom\$1)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/03/21 13:39

S5	0	(((solid adj state) semiconductor metal gate) near (layer film material)) with (no near more near "40.0" near angstrom\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:41
S6	0	(((solid adj state) semiconductor metal gate) near (layer film material)) with ("40.0" near angstrom\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:40
S7	0	(((solid adj state) semiconductor metal gate) near (layer film material)) and (no near more near "40.0" near angstrom\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:41
S8	646122	(((solid adj state) semiconductor metal gate) near (layer film material))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:41
S9	0	((no near more) less) near "40.0" near angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:42
S10	0	((no near more) less) near "40.0" near angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:42
S11	6	"40.0" near angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:43
S12	2356	"40" near angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:32
S13	993	S8 and S12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:44

S14	4	S13 and (metallurgical\$2 near bond\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:26
S15	12	("20020164846"   "3430109"   "3585714"   "4371406"   "4916513"   "4946800"   "5082793"   "5696402"   "6057584"   "6599781").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/21 13:48
S16	1	S13 and (atomic\$4 near smooth near surface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:56
S17	1	S12 and (atomic\$4 near smooth near surface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:25
S18	6	S12 and (metallurgical\$2 near bond\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 13:57
S19	18	S12 and (atomic\$4 near smooth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/22 08:09
S20	2	("5422305"   "5606177").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/21 14:09
S21	1	S12 and ((source drain) near pocket\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 14:17
S22	1632	S12 and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 14:17
S23	19	S22 and (atomic\$4 near2 surface)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/21 14:22

S24	646469	((solid adj state) semiconductor metal gate) near (layer film material))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/11/03 17:30
S25	2360	"40" near angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/22 08:09
S26	997	S24 and S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/22 08:09
S27	15	S26 and (atomic\$4 near smooth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/22 08:10
S28	2	("6599781").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/08/08 06:48
S29	8	(("6599781") or ("6057584") or ("5696402") or ("4371406")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/11/03 12:34